



40V 175°C P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C		
-40V	$29m\Omega$ @ $V_{GS} = -10V$	-8.0A		
	45mΩ @ V _{GS} = -4.5 V	-6.0A		

Features and Benefits

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Test in Production— Ensures More Reliable and Robust End Application
- Low R_{DS(ON)}—Ensures On State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

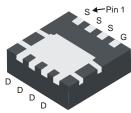
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

PowerDI3333-8

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

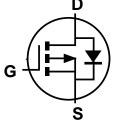
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.072 grams (Approximate)



Bottom View



Top View



Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging		
DMPH4029LFGQ-7	PowerDI3333-8	2000/Tape & Reel		
DMPH4029LFGQ-13	PowerDI3333-8	3000/Tape & Reel		

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds..
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



H29= Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)

March 2019



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-40	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ΙD	-8.0 -6.7	А
Continuous Drain Current (Note 7) VGS = -10V	Steady State	T_C = +25°C T_C = +70°C	ID	-22 -18	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 19	I _{DM}	-88	Α		
Maximum Continuous Body Diode Forward Current	Is	-2.0	Α		
Pulsed Source Current (380µs Pulse, Duty Cycle =	I _{SM}	-88	Α		
Avalanche Current (Note 8) L = 0.1mH	IAS	-25	Α		
Avalanche Energy (Note 8) L = 0.1mH	E _{AS}	32	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)		P_{D}	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	125	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\Theta JA}$	85	
Total Power Dissipation (Note 7)		P_D	2.8	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	ב	54	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\Theta JA}$	36	
Thermal Resistance, Junction to Case (Note 7)	$R_{\Theta JC}$	6		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

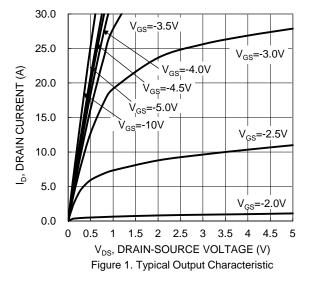
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-40		_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0		-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance			18	29	mΩ	$V_{GS} = -10V, I_D = -3A$	
Static Dialit-Source Off-Resistance	R _{DS(ON)}	_	23	45	11122	$V_{GS} = -4.5V, I_D = -3A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	1626	_	pF		
Output Capacitance	Coss	_	135	_	pF	$V_{DS} = -20V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	107	_	pF	11 = 1.0IVID2	
Gate Resistance	R_g		11	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	_	17	_	nC		
Total Gate Charge (V _{GS} = -10V)	Q_g		34	_	nC	\/ 20\/ I- 2A	
Gate-Source Charge	Q_{gs}	_	3.7	_	nC	$V_{DS} = -20V, I_{D} = -3A$	
Gate-Drain Charge	Q_{gd}	_	6.0	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	3.9	_	ns	V _{GS} = -10V, V _{DS} = -20V,	
Turn-On Rise Time	t _R	_	2.8	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	83	_	ns	$R_G = 3\Omega$, $I_D = -3A$	
Turn-Off Fall Time	t _F	_	30	_	ns	1	
Body Diode Reverse Recovery Time	t _{RR}	_	17.3	_	ns	I _F = -3A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	7.2	_	nC	$I_F = -3A$, $di/dt = 100A/\mu s$	

Notes:

- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.





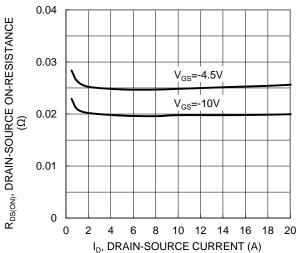


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

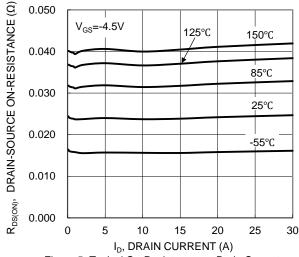


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

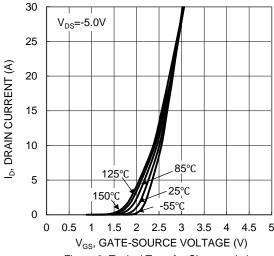
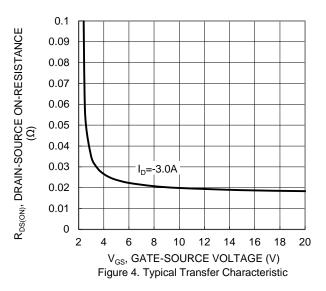


Figure 2. Typical Transfer Characteristic



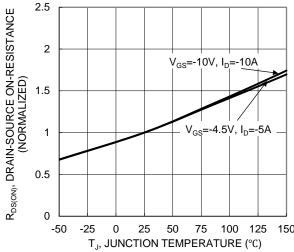


Figure 6. On-Resistance Variation with Temperature



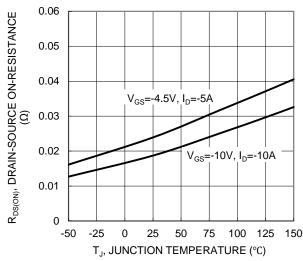
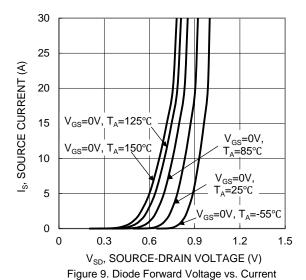
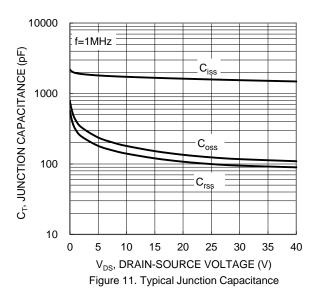


Figure 7. On-Resistance Variation with Temperature





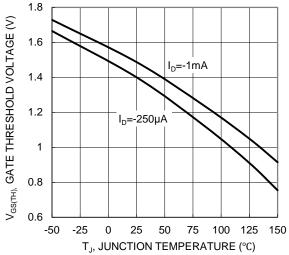


Figure 8. Gate Threshold Variation vs. Junction Temperature

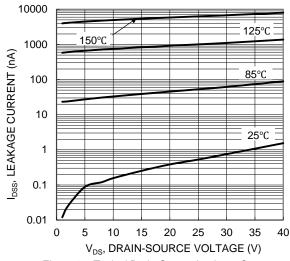
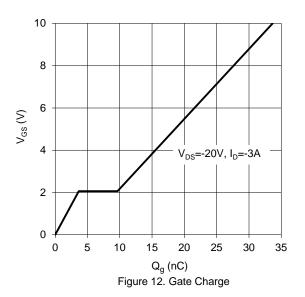
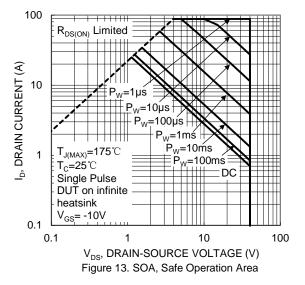


Figure 10. Typical Drain-Source Leakage Current vs. Voltage







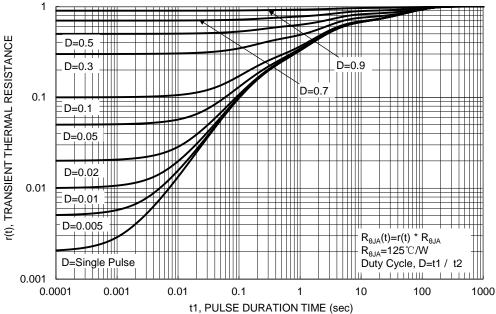


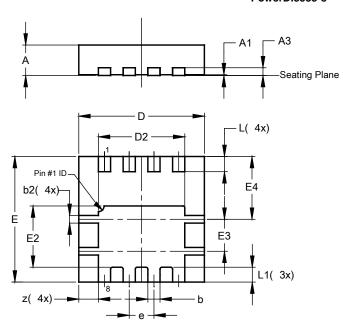
Figure 14. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

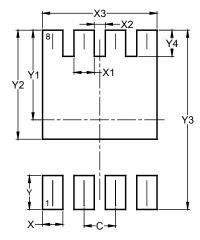


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A 3	1	1	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
E	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	-	-	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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